



580 Metallization Contact Layer
570 p ⁺ -InP Layer
560 <i>i</i> -InP Multiplication Layer
550 n-InP Field Control Layer
540 n-InGaAsP Grading Layer
530 <i>n</i> -InGaAs or <i>n</i> -InGaAsP Absorber
520 i-InGaAs or i-InGaAsP Absorber
510 n ⁺ -InP Buffer Layer
500 <i>n</i> ⁺ -InP Substrate

Figure 5

